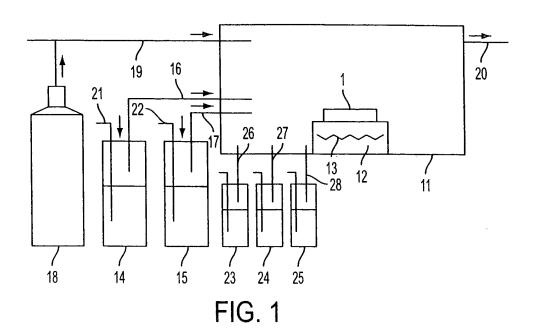
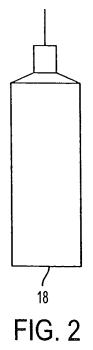
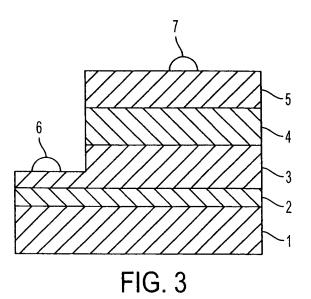


Rule 53(b) Continuation Appln. of Appln. No. 09/473,70 Inventor(s): Hideki HAYASHIDA, et al. Appln. No.: To Be Assigned; Filed: April 12, 2004 For: 'Ammonia For Use In Manufacture of GAN-Type Compound Semiconductor And Method For Manufacturing GAN-Type Compound Semiconductor SUGHRUE Tel. No. 202-293-7060; Ref. No. Q81061 | 1 of 2





Rul* 53(b) Continuation Appln. of Appln. No. 09/473,708 In. (s): Hideki HAYASHIDA, et al. Appl. No.: To Be Assigned; Filed: April 12, 2004 For: Ammonia For Use In Manufacture of GAN-Type Compound Semiconductor And Method For Manufacturing GAN-Type Compound Semiconductor SUGHRUE Tel. No. 202-293-7060; Ref. No. Q81061 2 of 2





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